Refine Search

Search Results -

Terms	Documents
L27	0

Database:

```
US Pre-Grant Publication Full-Text Database
US Patents Full-Text Database
US OCR Full-Text Database
EPO Abstracts Database
JPO Abstracts Database
Derwent World Patents Index
IBM Technical Disclosure Bulletins
```

Search

L28

[Refine Search]

[Recall Text ⬍]　[Clear]　[Interrupt]

Search History

DATE: Thursday, January 27, 2005　　Printable Copy　　Create Case

Set Name side by side	Query	Hit Count	Set Name result set
	DB=TDBD; PLUR=YES; OP=OR		
L28	L27	0	L28
	DB=DWPI; PLUR=YES; OP=OR		
L27	L26	0	L27
	DB=JPAB; PLUR=YES; OP=OR		
L26	L25	0	L26
	DB=EPAB; PLUR=YES; OP=OR		
L25	L24	0	L25
	DB=USOC; PLUR=YES; OP=OR		
L24	L23	0	L24
	DB=USPT; PLUR=YES; OP=OR		
L23	L22	0	L23
	DB=PGPB; PLUR=YES; OP=OR		
L22	L21	0	L22

DB=USPT; PLUR=YES; OP=OR

L21	"double gate CMOS" and "trench gate"	0	L21
L20	"double gate CMOS"	11	L20
L19	6197672	2	L19
L18	5899770	4	L18
L17	L16	0	L17
L16	"trench gate" same (("first gate" near5 (polysilicon)) same ("second gate" near5 (polysilicon)))	0	L16

DB=TDBD; PLUR=YES; OP=OR

| L15 | L14 | 0 | L15 |

DB=JPAB; PLUR=YES; OP=OR

| L14 | L13 | 0 | L14 |

DB=EPAB; PLUR=YES; OP=OR

| L13 | L12 | 0 | L13 |

DB=USOC; PLUR=YES; OP=OR

| L12 | L11 | 0 | L12 |

DB=USPT; PLUR=YES; OP=OR

| L11 | "trench gate" same (("first gate" near5 (N near3 polysilicon)) same ("second gate" near5 (P near3 polysilicon))) | 0 | L11 |
| L10 | "trench gate" same ("first gate" near5 "n type") same ("second gate" near5 "p type") | 0 | L10 |

DB=TDBD; PLUR=YES; OP=OR

| L9 | L8 | 0 | L9 |

DB=DWPI; PLUR=YES; OP=OR

| L8 | L7 | 0 | L8 |

DB=JPAB; PLUR=YES; OP=OR

| L7 | L6 | 0 | L7 |

DB=EPAB; PLUR=YES; OP=OR

| L6 | L5 | 0 | L6 |

DB=PGPB; PLUR=YES; OP=OR

| L5 | L4 | 0 | L5 |

DB=USOC; PLUR=YES; OP=OR

| L4 | L3 | 0 | L4 |

DB=USPT; PLUR=YES; OP=OR

L3	L2 and ("first gate" near6 fermi) and ("second gate" near5 fermi)	0	L3
L2	"trench gate" same (multigate or double gate)	1115	L2
L1	6586290	3	L1

END OF SEARCH HISTORY